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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: July 10, 2006 (use as many sheets as necessary)				Complete if Known	
Sheet	1	of	1	Application Number	Unassigned
				Filing Date	12/28/2004
				First Named Inventor	Kazuya UEJIMA
				Group Art Unit	Unassigned 4136
				Examiner Name	Unassigned Duy T Nguyen
				Attorney Docket Number	065686-0163

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/D.N./	A1	2004/0135210	A1	NOGUCHI et al.	07-15-2004	
/D.N./	A2	2003/0227029	A1	LOCHTEFELD et al.	12-11-2003	
/D.N./	A3	6,633,066	B1	BAE et al.	10-14-2003	
/D.N./	A4	6,190,975	B1	KUBO et al.	02-20-2001	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
/D.N./	A5	JP	2002-237590	A	UNIV TOHOKU	08-23-2002		A
/D.N./	A6	JP	2001-217433		SAMSUNG ELECTRONICS CO. LTD.	08-10-2001		A
/D.N./	A7	JP	2000-286418		HITACHI LTD.	10-13-2000		A
/D.N./	A8	JP	10-270685		SONY CORP.	10-09-1998		A
/D.N./	A9	JP	10-214906		MATSUSHITA ELECTRIC IND. CO. LTD.	08-11-1998		A
/D.N./	A10	JP	10-106966		NIPPON STEEL CORP.	04-24-1998		A
/D.N./	A11	EP	1 174 928	A1	HITACHI LTD.	01-23-2002		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.						T ⁶
/D.N./	A12	J.L. HOYT et al., "Strained Silicon MOSFET Technology," IEDM 2002, pp. 23-26.						
/D.N./	A13	M. TAMURA et al., "Secondary Defects in 1-10 keV As- and BF2-implanted Si," International Conference on Ion Implantation Technology Proceedings, pp. 744-747.						
/D.N./	A14	H.C. -H. WANG et al., "Substrate-Strained Silicon Technology: Process Integration," IEDM 2003, pp. 61-64.						

Examiner Signature	/Duy Nguyen/	Date Considered	10/29/2008
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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